





# Study of Electronegativity in Inductively Coupled Radio-Frequency Plasma with Langmuir Probe

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## About Queen's

#### Director: Prof. Bill Graham



#### Cooperator: Mr. Mujahid



#### Main building of Queen's



# Introduction to ICP





# Oxygen ICP application

Semiconductor manufacture

### Ashing:

Oxygen +polymers /organics  $\rightarrow CO_2 + H_2O$ 



# Oxygen ICP characteristics



### Negative ions: $O^{-}, O_{2}^{-}, O_{3}^{-}, etc$

## Two operation regimes:

E-mode: low power, low density, capacitive discharge. H-mode: high power, high density, inductively discharge.

#### E-H transition:

change of electron density, EEDF, coil current, light emission, etc.

# Photo-detachment measuring system

### GEC reference cell



Schematic of photo-detachment measurement system

Electrode diameter: 165.1 mm Electrode gap: 40.5 mm

## Photo-detachment diagnostics

Diagnostics principle:

Photo-detachment electron current

electron affinities: O<sup>-</sup>:1.46 eV; O<sub>2</sub><sup>-</sup>:0.44 eV Nd:YAG laser(532 nm): hv=2.33 eV

 $A^{-}+hv=A+e$ 



Suffice to photo-detach both species

#### Advantages:

- Less perturbing
- Better time resolution
- Capacity of measuring ion temperature

# Photodetachment fraction Vs laser energy

## Experimental:

Negative ion density:

 $\frac{\Delta I_e}{I_e} = \frac{n_-}{n_e}$ 

 $I_e$ : probe current  $n_e$ : background density  $\Delta I_e$ : instantaneous current

### Theoretical:

Photo-detachment fraction:

 $\frac{\Delta n_{-}}{n_{-}} = 1 - \exp{(-\frac{E}{S}\frac{\sigma_{pd}}{h\nu})}$ 

E:incident laser power S:beam cross-sectional area  $\sigma_{pd}$ : photo-detachment cross section of negative ion

#### Deviate from theory:

thermionic electron emission laser ablation of the probe surface



# Electronegativity Vs probe bias



Electronegativity (blue), Negative ion current (black) and electron current (red) against probe bias voltage in capacitive mode.

Electronegativity (black), Negative ion current (red) and electron current (green) against probe bias voltage in inductive mode.



## Electronegativity against pressure

Capacitive mode



#### Peak electronegativity when RF power fixed:

O<sup>-</sup>is produced by dissociative attachment of  $O_2$  and destroyed by ion-ion recombination at low pressures. At higher pressures it is lost due to detachment.

Electronegativity decreased when RF power increase: Electron density increases while negativity ion density is almost constant

## Electronegativity against pressure Compared with simulation





Figure 3.2. Core electron density  $n_{e0}$  versus pressure at 500, 1000 and 2000 W of absorbed power.



Figure 3.4. Average electronegativity  $\vec{\alpha}$  versus pressure at 500, 1000 and 2000 W of absorbed power.

Figure 3.3. Average negative ion density  $\bar{n}_{cr}$  versus pressure at 500, 1000 and 2000 W of absorbed power.

#### From Corrmac. Corr Ph.Dthesis

## Conclusion & future work

#### < Conclusion: >

Laser energy, laser diameter and probe bias voltage were calibrated and suitable parameters were selected for photo-detachment measurement.

> Electrongativity were measured at different positions in capacitive mode.

 $\succ$  The relationship between electronegaticity and pressure & RF power is consistent with simulation.

#### < Future work: >

Measuring electronegativity against pressure in inductively mode













## Electronegativity against pressure

### Inductive mode 1.25 cm from lower electrode



The relationship is not clear and should do again.



## Electronegativity against pressure Compared with simulation





Global model

From Corrmac. Corr thesis

## Self introduction

Name: Bin Huang (黄 斌)

Hometown: Suzhou, China (蘇州,中国)

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Research in Tokyo Tech:
Xe gas jet type Z-pinch EUV source
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Research in Queen's: Oxygen radio-frequency ICP

# Oxygen Inductively Coupled Plasma



#### Two operation regimes:

E-mode: low power, low density, capacitive discharge. H-mode: high power, high density, inductively discharge.

Negative ions:  $O^{-}, O_{2^{-}}, O_{3^{-}}, etc$ 

O2- is less than 10%

< Application: >

surface modification
fabrication of chips
thin film deposition

#### E-H transition:

change of electron density, EEDF, coil current, light emission, etc.